1. General description

PNP high-voltage low V_{CEsat} transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8215Z

2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain h_{FE} at high I_C
- Medium power SMD plastic package

3. Applications

- LED driver for LED chain module
- LCD backlighting
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-150	V
I _C	collector current		-	-	-2	Α
h _{FE}	DC current gain	V_{CE} = -10 V; I_{C} = -100 mA; pulsed; t_{p} ≤ 300 μs; δ = 0.02; T_{amb} = 25 °C	100	180	-	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C
2	С	collector		В
3	Е	emitter		- Tw
4	С	collector		Ė
			SC-73 (SOT223)	sym028



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6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBHV9215Z		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223

7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV9215Z	V9215Z

8. Limiting values

Table 5. Limiting values

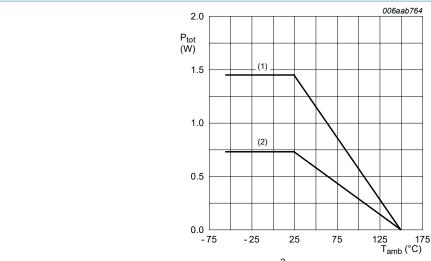
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-200	V
V_{CEO}	collector-emitter voltage	open base		-	-150	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-4	А
I _{BM}	peak base current			-	-500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.73	W
			[2]	-	1.45	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

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- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	170	K/W
	junction to ambient		[2]	-	-	85	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

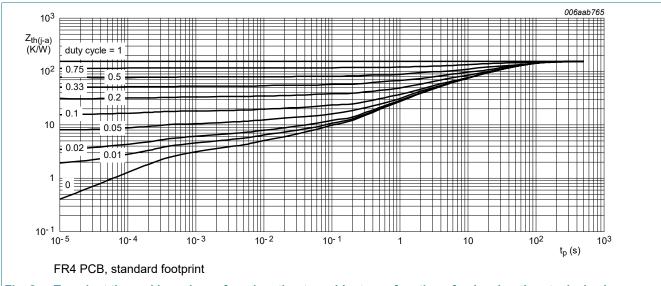
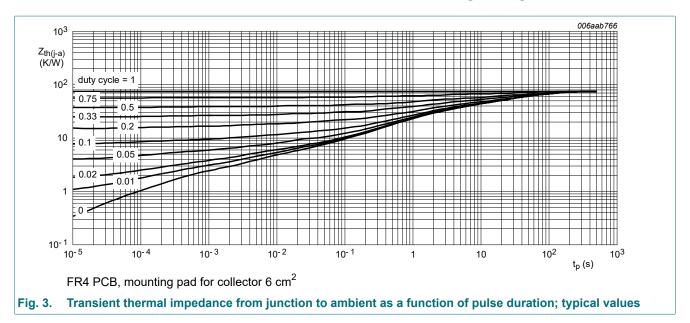


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -120 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -120 V; I _E = 0 A; T _j = 150 °C	-	-	-10	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = -120 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -4 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -10 V; I_{C} = -100 mA; pulsed; t_{p} ≤ 300 μs; δ = 0.02; T_{amb} = 25 °C	100	180	-	
		V_{CE} = -10 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ = 0.02; T_{amb} = 25 °C	80	155	-	
		V_{CE} = -10 V; I_{C} = -1.5 A; pulsed; t_{p} ≤ 300 μs; δ = 0.02; T_{amb} = 25 °C	70	140	-	
		V_{CE} = -10 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ = 0.02; T_{amb} = 25 °C	60	120	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -100 mA; I_B = -20 mA; pulsed; $t_p \le$ 300 μs; δ = 0.02; T_{amb} = 25 °C	-	-25	-50	mV
		I_C = -1 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ = 0.02; T_{amb} = 25 °C	-	-110	-190	mV
		I_C = -1.5 A; I_B = -300 mA; pulsed; $t_p \le$ 300 μs; δ = 0.02; T_{amb} = 25 °C	-	-155	-270	mV
		I_C = -2 A; I_B = -400 mA; pulsed; t_p ≤ 300 μs; δ = 0.02; T_{amb} = 25 °C	-	-200	-350	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = -2 A; I_B = -400 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	100	175	mΩ
V _{BEsat}	base-emitter saturation voltage		-	-1	-1.15	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
t _d	delay time	$V_{CC} = -6 \text{ V}; I_C = -0.5 \text{ A}; I_{Bon} = -0.1 \text{ A};$	-	20	-	ns	
t _r	rise time	I _{Boff} = 0.1 A; T _{amb} = 25 °C	-	105	-	ns	
t _{on}	turn-on time			-	125	-	ns
t _s	storage time		-	875	-	ns	
t _f	fall time		-	150	-	ns	
t _{off}	turn-off time		-	1025	-	ns	
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	-	35	-	MHz	
C _c	collector capacitance	V _{CB} = -20 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	30	-	pF	
C _e	emitter capacitance	V_{EB} = -0.5 V; I_{C} = 0 A; i_{c} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	530	-	pF	

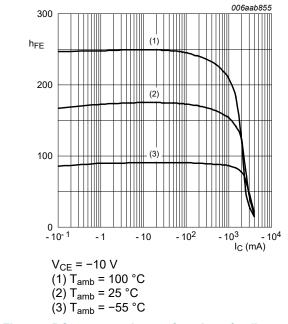


Fig. 4. DC current gain as a function of collector current; typical values

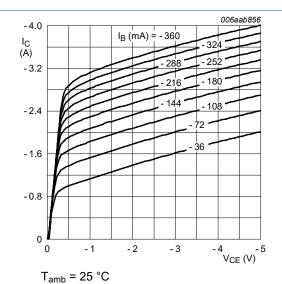
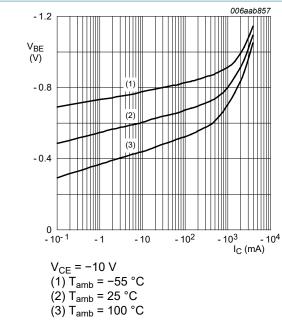


Fig. 5. Collector current as a function of collectoremitter voltage; typical values

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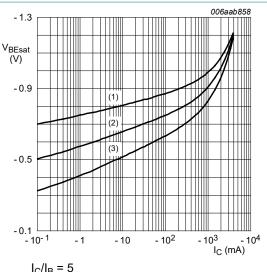


$$(1) T_{amb} = -55 ° ($$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 5$$

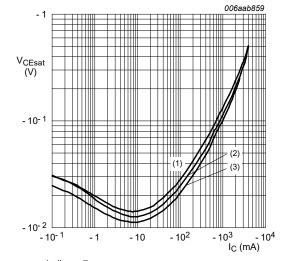
(1)
$$T_{amb} = -55 \,^{\circ}\text{C}$$

(2) $T_{amb} = 25 \,^{\circ}\text{C}$
(3) $T_{amb} = 100 \,^{\circ}\text{C}$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



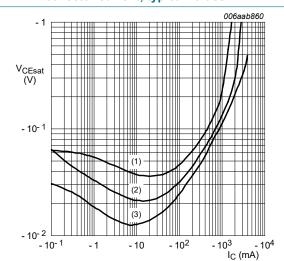
$$I_{\rm C}/I_{\rm B}=5$$

$$(1) T_{amb} = 100 °C$$

$$(2) T_{amb} = 25 °C$$

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1)
$$I_C/I_B = 20$$

(2)
$$I_C/I_B = 10$$

(3)
$$I_C/I_B = 5$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

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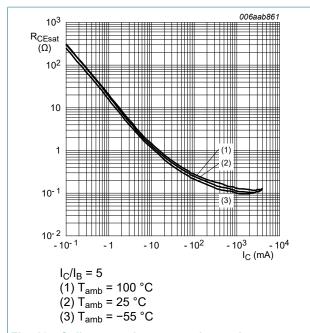


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

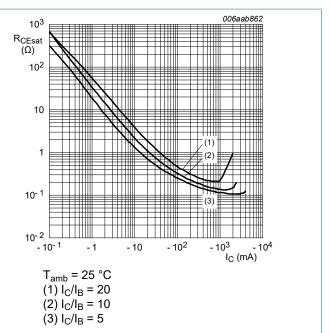
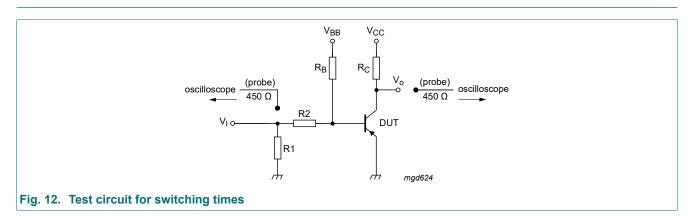


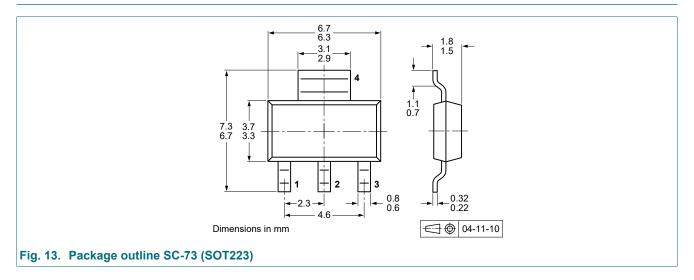
Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information

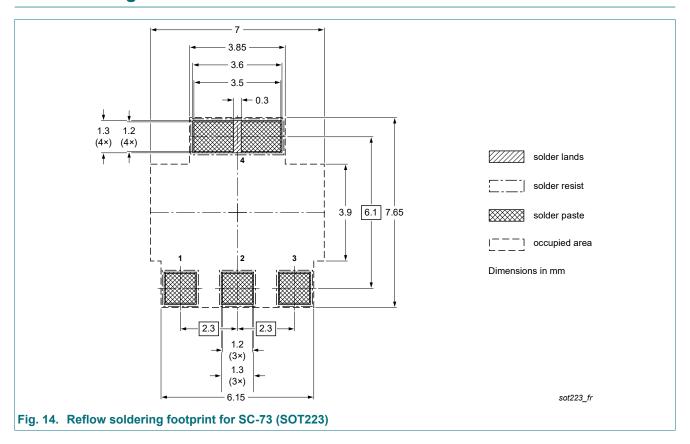


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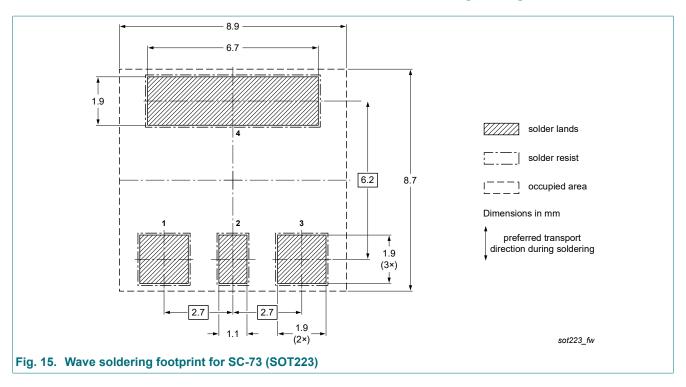
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBHV9215Z v.3	20241009	Product data sheet	-	PBHV9215Z v.2				
Modifications:	 Product(s) changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s). 							
PBHV9215Z v.2	20230717	Product data sheet	-	PBHV9215Z_1				
PBHV9215Z_1	20091211	Product data sheet	-	-				

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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